MOSFETs Silicon N-channel MOS (U-MOSVII-H)

# TPN30008NH

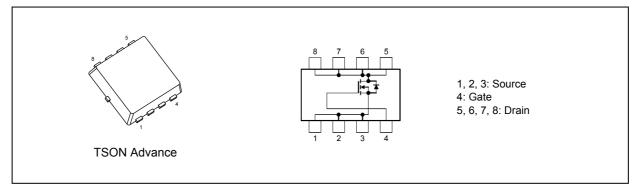
#### 1. Applications

- DC-DC Converters
- Switching Voltage Regulators
- Motor Drivers

#### 2. Features

- (1) Small, thin package
- (2) High-speed switching
- (3) Small gate charge:  $Q_{SW} = 4.1 \text{ nC}$  (typ.)
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 25 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (5) Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 80 \ V)$
- (6) Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 0.1 mA)

#### 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) ( $T_a = 25 \,^{\circ}C$ unless otherwise specified)

Characteris	Symbol	Rating	Unit		
Drain-source voltage			V <sub>DSS</sub>	80	V
Gate-source voltage			V <sub>GSS</sub>	±20	1
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	I <sub>D</sub>	22	A
Drain current (DC)	(T <sub>c</sub> = 25 °C)	(Note 1)	I <sub>D</sub>	9.6	1
Drain current (pulsed)	(t = 1 ms)	(Note 1)	I <sub>DP</sub>	47	1
Power dissipation	(T <sub>c</sub> = 25 °C)		PD	27	W
Power dissipation	(t = 10 s)	(Note 3)	PD	1.9	W
Power dissipation	(t = 10 s)	(Note 4)	P <sub>D</sub>	0.7	W
Single-pulse avalanche energy		(Note 5)	E <sub>AS</sub>	29	mJ
Avalanche current			I <sub>AR</sub>	9.6	A
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	1

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal resistance	(T <sub>c</sub> = 25 °C)		R <sub>th(ch-c)</sub>	4.62	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R <sub>th(ch-a)</sub>	65.7	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 4)	R <sub>th(ch-a)</sub>	178	

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Limited by silicon chip capability.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V\_DD = 60 V, T\_ch = 25 °C (initial), L = 0.27 mH, I\_{AR} = 9.6 A

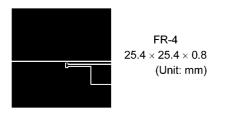


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

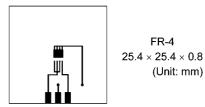


Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

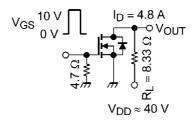
#### 6. Electrical Characteristics

#### 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±20 V, $V_{DS}$ = 0 V	_	_	±0.1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V	_		10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	80		_	V
Drain-source breakdown voltage	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	60	_	_	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.1 mA	2.0		4.0	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.8 A	-	25	30	mΩ

#### 6.2. Dynamic Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	710	920	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	10	50	
Output capacitance	C <sub>oss</sub>		_	170	_	
Gate resistance	rg	—	_	0.6	1.1	Ω
Switching time (rise time)	t <sub>r</sub>	See Fig. 6.2.1	_	3.8	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	11	_	
Switching time (fall time)	t <sub>f</sub>		_	3.6	_	
Switching time (turn-off time)	t <sub>off</sub>		_	14	_	



Duty  $\leq$  1%, t<sub>w</sub> = 10  $\mu$ s

Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics ( $T_a = 25$ °C unless otherwise specified)

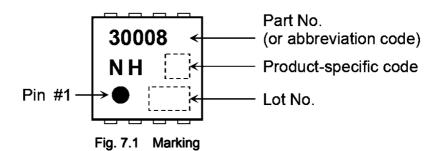
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD}\approx 40~V,~V_{GS}$ = 10 V, I <sub>D</sub> = 9.6 A	—	11	—	nC
Gate-source charge 1	Q <sub>gs1</sub>			3.7		
Gate-drain charge	Q <sub>gd</sub>			2.6	_	
Gate switch charge	Q <sub>SW</sub>			4.1		

#### 6.4. Source-Drain Characteristics ( $T_a = 25$ °C unless otherwise specified)

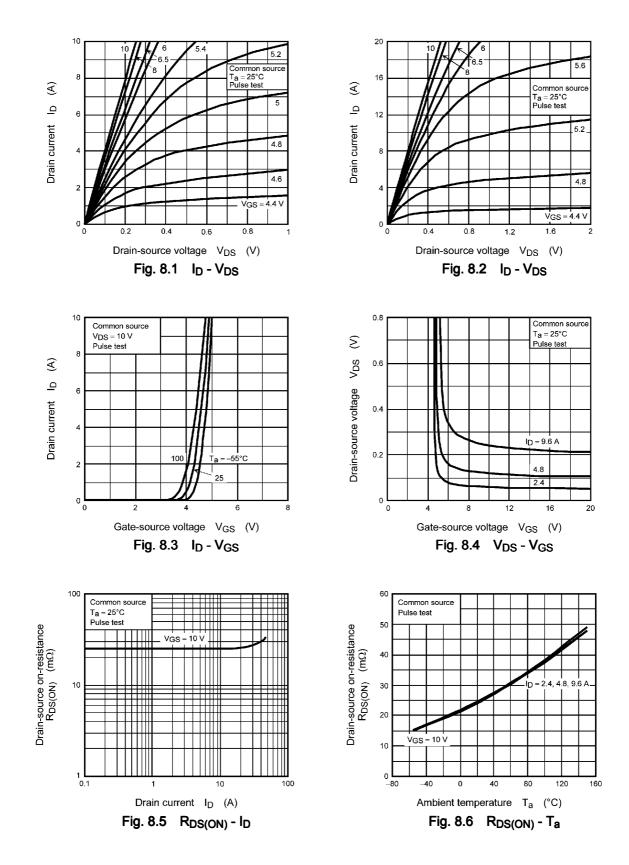
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (N	Note 6)	I <sub>DRP</sub>	—	_	_	47	Α
Diode forward voltage		V <sub>DSF</sub>	I <sub>DR</sub> = 9.6 A, V <sub>GS</sub> = 0 V	_	_	-1.2	V

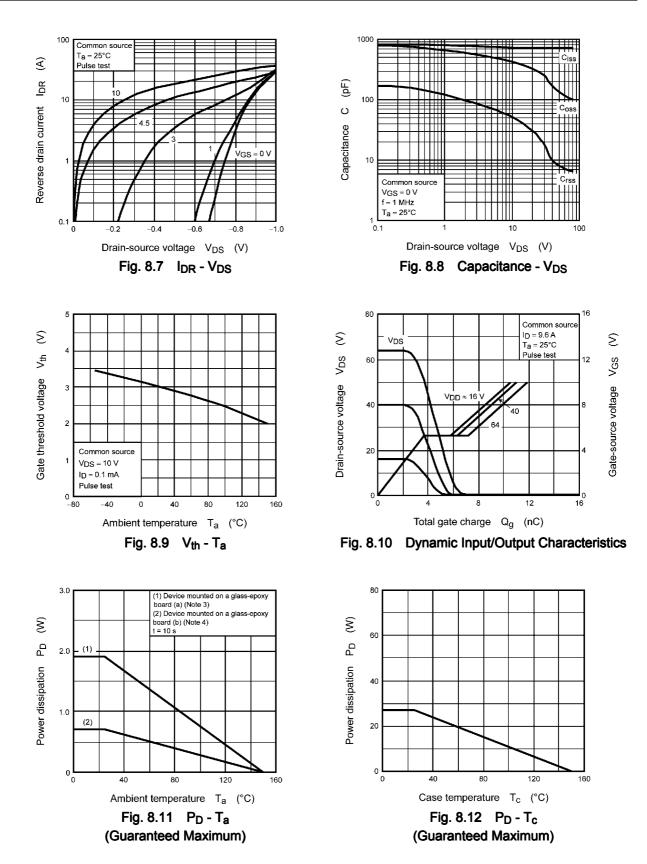
Note 6: Ensure that the channel temperature does not exceed 150 °C.

#### 7. Marking

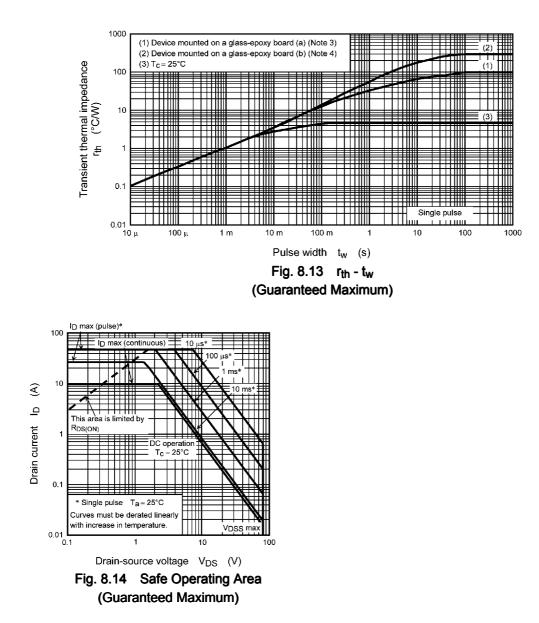


#### 8. Characteristics Curves (Note)









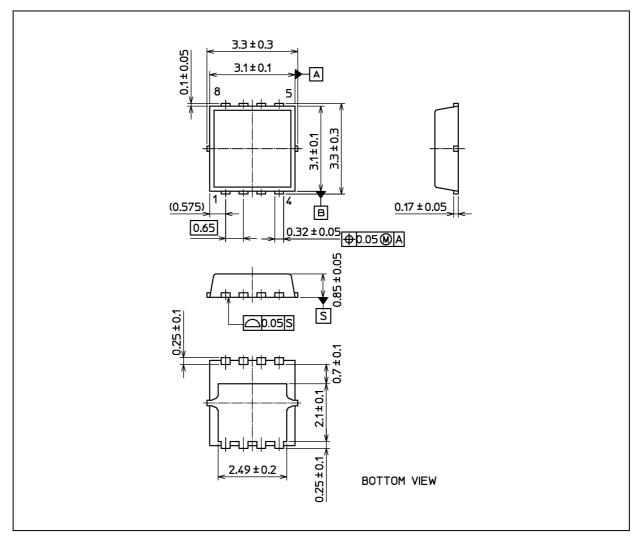
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### TPN30008NH

#### **Package Dimensions**

Unit: mm



Weight: 0.02 g (typ.)

Package Name(s)
TOSHIBA: 2-3X1S
Nickname: TSON Advance

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